

## 三态输出-移位存储总线寄存器

### 简要说明

CD4094 是带输出锁存和三态控制的串入/并出高速转换器，具有使用简单、功耗低、驱动能力强和控制灵活等优点。

CD4094 的引脚定义如图。其中(1)脚为锁存端，(2)脚为串行数据输入端，(3)脚为串行时钟端。

(1)脚为高电平时，8位并行输出口Q1~Q8在时钟的上升沿随串行输入而变化；(1)脚为低电平时，输出锁定。利用锁存端可方便地进行片选和级联输出控制。

(15)脚为并行输出状态控制端，(15)脚为低电平时，并行输出端处在高阻状态。

在用CD4094作显示输出时，可使显示数码闪烁。

(9)脚QS、(10)脚Q'S是串行数据输出端，用于级联。QS端在第9个串行时钟的上升沿开始输出，Q'S端在第9个串行时钟的下降沿开始输出。

CD4094 提供了DIP16封装形式。

引脚图

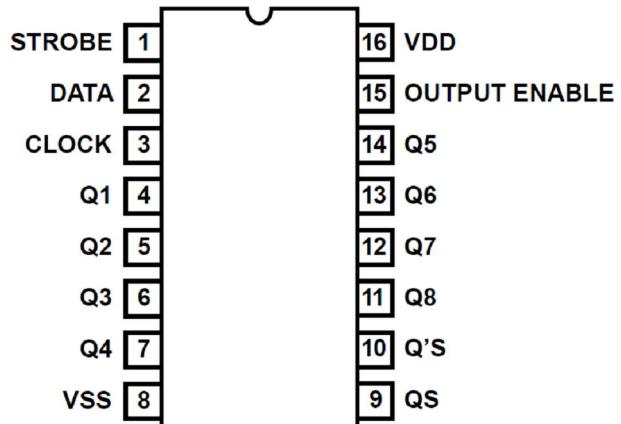
TOP VIEW

### 主要特点：

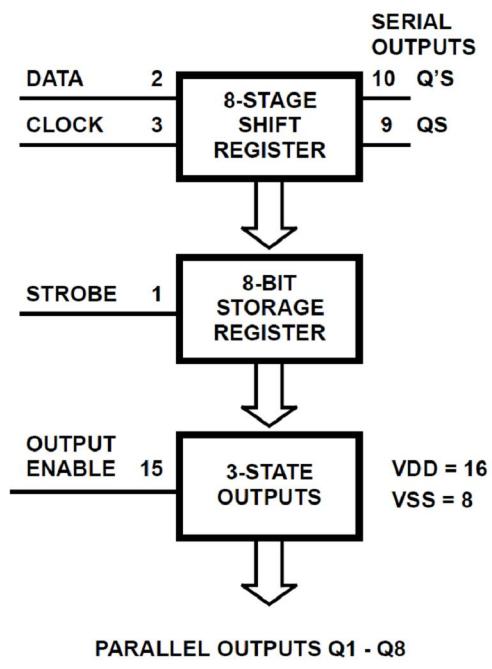
- 宽工作电源+3V~15V
- 抗干扰性能高 0.45 VDD (typ.)
- 低功耗，TTL兼容，  
可驱动两路74L或1路74LS
- 三态输出
- 全静态工作 (15V)

### 主要应用：

- 串并数据转换
- 遥控器保持寄存器
- 双级转移，保持，和总线应用

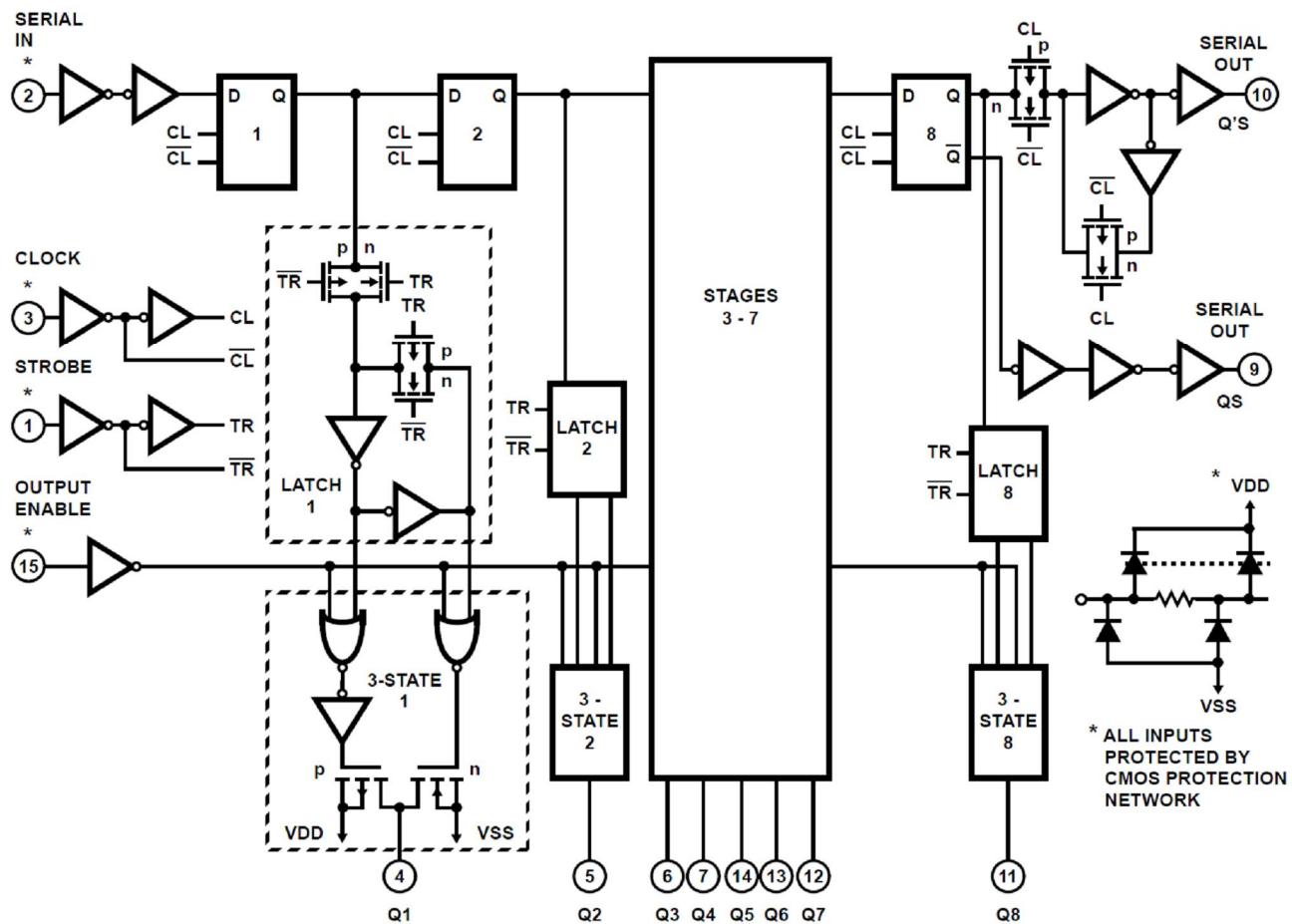


### 功能框图



(TERMINALS 4, 5, 6, 7, 14, 13, 12, 11, RESPECTIVELY)

### 逻辑框图（整体）



### 真值表

TRUTH TABLE

CL $\Delta$	OUTPUT ENABLE	STROBE	DATA	PARALLEL OUTPUTS		SERIAL OUTPUTS	
				Q1	QN	QS*	Q'S
/	0	X	X	OC	OC	Q7	NC
/	0	X	X	OC	OC	NC	Q7
/	1	0	X	NC	NC	Q7	NC
/	1	1	0	0	QN-1	Q7	NC
/	1	1	1	1	QN-1	Q7	NC
/	1	1	1	NC	NC	NC	Q7

$\Delta$  = Level Change

Logic 1 = High

X = Don't Care

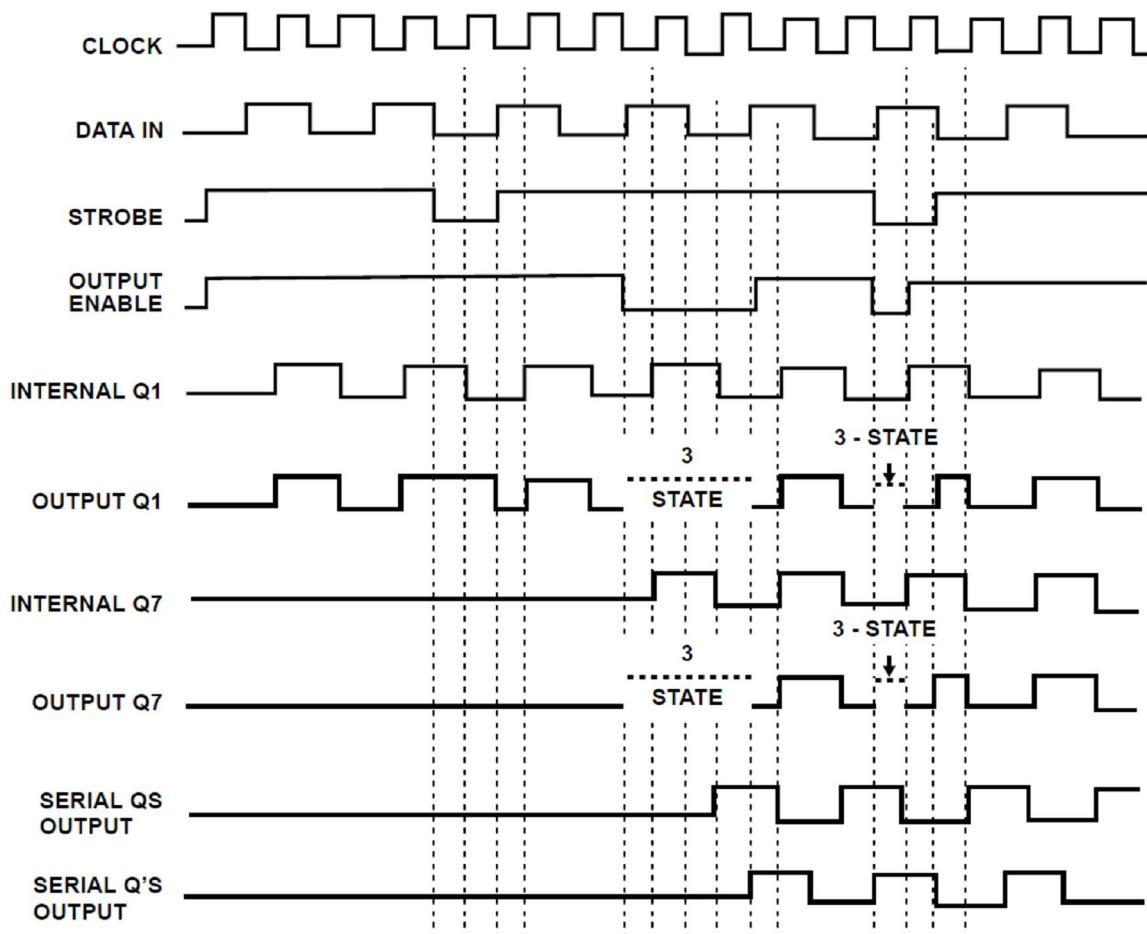
Logic 0 = Low

NC = No Change

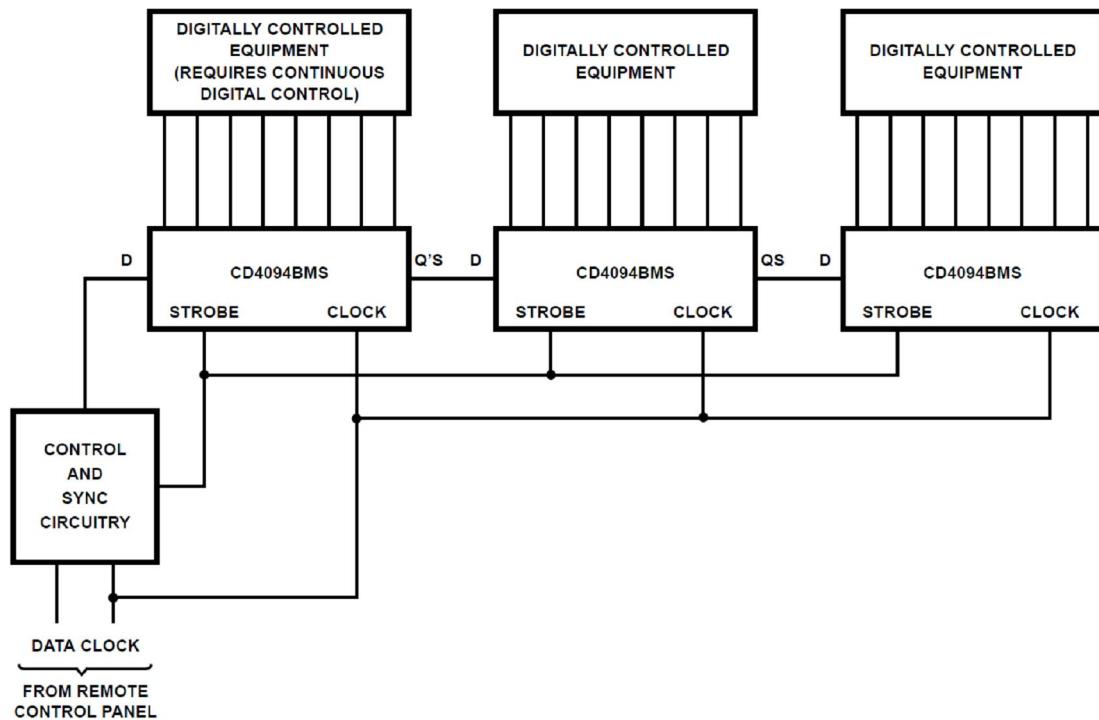
OC = Open Circuit

\* At the positive clock edge information in the 7th shift register stage is transferred to the 8th register stage and the QS output

### 时序图



## 多级控制寄存应用



## 参数特性

### Absolute Maximum Ratings (Note 1)

(极限参数)

(Note 2)

DC Supply Voltage ( $V_{DD}$ )

-0.5 to +18 V<sub>DC</sub>

-0.5 to  $V_{DD}$  +0.5 V<sub>DC</sub>

( $T_S$ )

-55°C to +150°C

500 mW

Lead Temperature ( $T_L$ )

(Soldering, 10 seconds)

260°C

### Recommended Operating Conditions (Note 2)

(推荐工作条件)

DC Supply Voltage ( $V_{DD}$ )

+3 V<sub>DC</sub> to +15 V<sub>DC</sub> Input Voltage ( $V_{IN}$ )

Input Voltage ( $V_{IN}$ )

0 to  $V_{DD}$  V<sub>DC</sub> Storage Temperature

Operating Temperature Range ( $T_A$ )

0°C to +70°C Power Dissipation ( $P_D$ )

**Note 1:** "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed, they are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

**Note 2:** VSS = 0V unless otherwise specified.

### DC Electrical Characteristics (Note 2)

符号	参数	测试条件	温度			单位
			Min	Typ	Max	

I <sub>DD</sub>	Quiescent Device Current	V <sub>DD</sub> = 5V V <sub>DD</sub> = 10V V <sub>DD</sub> = 15V			5 10 20	µA
V <sub>OL</sub>	LOW Level Output Voltage	I <sub>O</sub>   < 1.0 µA V <sub>DD</sub> = 5V V <sub>DD</sub> = 10V V <sub>DD</sub> = 15V 10V		0 0 0	0.05 0.05 0.05	V
V <sub>OH</sub>	HIGH Level Output Voltage	I <sub>O</sub>   < 1.0 µA V <sub>DD</sub> = 5V V <sub>DD</sub> = 10V V <sub>DD</sub> = 15V V <sub>DD</sub>	4.95 9.95 14.95	5 10 15		V
V <sub>IL</sub>	LOW Level Input Voltage	I <sub>O</sub>   < 1.0 µA V <sub>DD</sub> = 5V, V <sub>O</sub> = 0.5V or 4.5V V <sub>DD</sub> = 10V, V <sub>O</sub> = 1.0V or 9.0V V <sub>DD</sub> = 15V, V <sub>O</sub> = 1.5V or 13.5V			1.5 3.0 4.0	V
V <sub>IH</sub>	HIGH Level Input Voltage	I <sub>O</sub>   < 1.0 µA V <sub>DD</sub> = 5V, V <sub>O</sub> = 0.5V or 4.5V V <sub>DD</sub> = 10V, V <sub>O</sub> = 1.0V or 9.0V V <sub>DD</sub> = 15V, V <sub>O</sub> = 1.5V or 13.5V	3.5 7.0 11.0			V
I <sub>OL</sub>	LOW Level Output Current (Note 3)	V <sub>DD</sub> = 5V, V <sub>O</sub> = 0.4V V <sub>DD</sub> = 10V, V <sub>O</sub> = 0.5V V <sub>DD</sub> = 15V, V <sub>O</sub> = 1.5V	0.44 1.1 3			mA
I <sub>OH</sub>	HIGH Level Output Current (Note 3)	V <sub>DD</sub> = 5V, V <sub>O</sub> = 4.6V V <sub>DD</sub> = 10V, V <sub>O</sub> = 9.5V V <sub>DD</sub> = 15V, V <sub>O</sub> = 13.5V			-0.44 -1.1 -3	mA
I <sub>IN</sub>	Input Current	V <sub>DD</sub> = 15V, V <sub>IN</sub> = 0V V <sub>DD</sub> = 15V, V <sub>IN</sub> = 15V			-0.3 0.3	µA
I <sub>OZ</sub>	3-STATE Output Leakage Current	V <sub>DD</sub> = 15V, V <sub>IN</sub> = 0V or 15V			1	µA

Note 3: I<sub>OL</sub> and I<sub>OH</sub> are tested one output at a time.

**AC Electrical Characteristics (Note 5)**

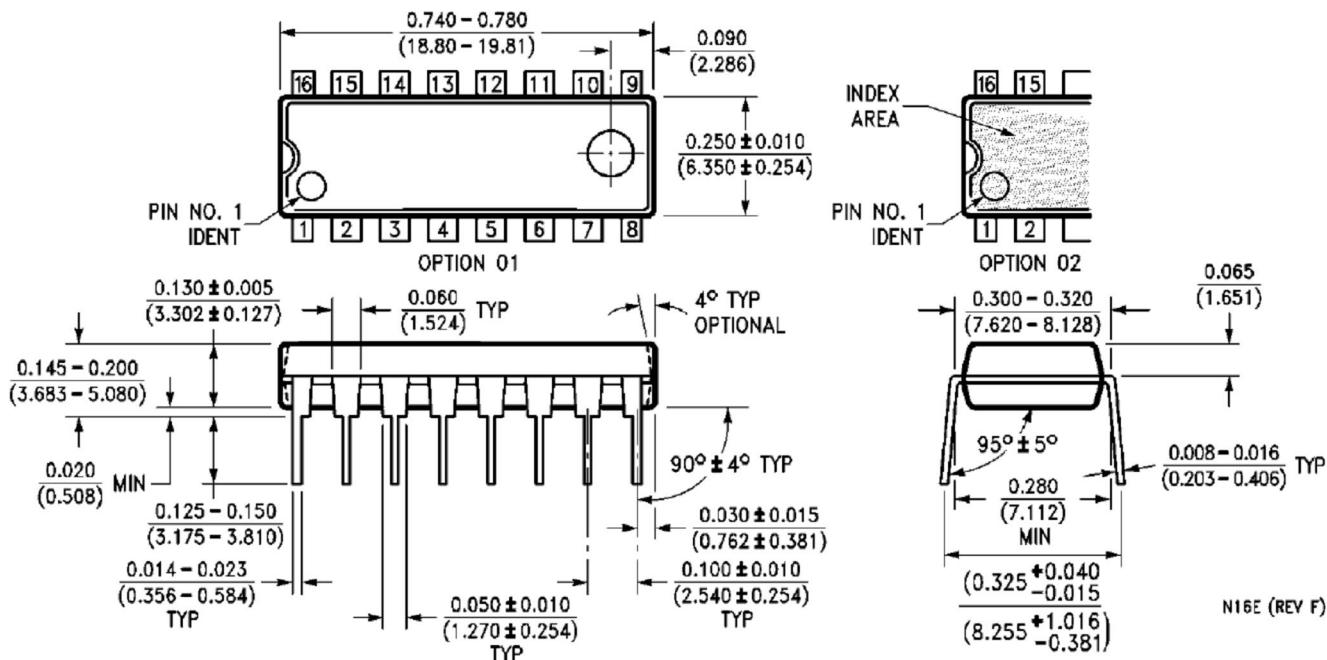
TA=25 C, CL =0 pF

<b>Symbol</b>	<b>Parameter</b>	<b>Conditions</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Units</b>
tPHL, tPLH	Propagation Delay Clock to QS	VDD=5.0V		300	600	ns
		VDD=10V		125	250	
		VDD=15V		95	190	
tPHL, tPLH	Propagation Delay Clock to Q	VDD=5.0V		230	460	ns
		VDD=10V		110	220	
		VDD=15V		75	150	
tPHL, tPLH	Propagation Delay Clock to Parallel Out	VDD=5.0V		420	840	ns
		VDD=10V		195	390	
		VDD=15V		135	270	
tPHL, tPLH	Propagation Delay Strobe to Parallel Out	VDD=5.0V		290	580	ns
		VDD=10V		145	290	
		VDD=15V		100	200	
tPHZ	Propagation Delay HIGH Level to HIGH Impedance	VDD=5.0V		140	280	ns
		VDD=10V		75	150	
		VDD=15V		55	110	
tPLZ	Propagation Delay LOW Level to HIGH Impedance	VDD=5.0V		140	280	ns
		VDD=10V		75	150	
		VDD=15V		55	110	
tPZH	Propagation Delay HIGH Impedance to HIGH Level	VDD=5.0V		140	280	ns
		VDD=10V		75	150	
		VDD=15V		55	110	
tPZL	Propagation Delay HIGH Impedance to LOW Level	VDD=5.0V		140	280	ns
		VDD=10V		75	150	
		VDD=15V		55	110	
tTHL, tTLH	Transition Time	VDD=5.0V		100	200	ns
		VDD=10V		50	100	
		VDD=15V		40	80	
tSU	Set-Up Time Data to Clock	VDD=5.0V	80	40		ns
		VDD=10V	40	20		
		VDD=15V	20	10		
tr, tf	Maximum Clock Rise and Fall Time	VDD=5.0V	1			ns
		VDD=10V	1			
		VDD=15V	1			
tPC	Minimum Clock Pulse Width	VDD=5.0V	200	100		ns
		VDD=10V	100	50		
		VDD=15V	83	40		
tPS	Minimum Strobe Pulse Width	VDD=5.0V	200	100		ns
		VDD=10V	80	40		
		VDD=15V	70	35		

fmax	Maximum Clock Frequency	VDD=5.0V VDD=10V VDD=15V	1.5 3.0 4.0	3.0 6.0 8.0		MHz MHz MHz
CIN	Input Capacitance	Any Input		5.0	7.5	pF

Note 5: AC Parameters are guaranteed by DC correlated testing.

### 相关封装信息



16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide  
Package Number N16E